

SANYO Semiconductors DATA SHEET

2SB1508 / 2SD2281 — High-Current Switching Applications

Applications

· Relay drivers, high-speed inverters, converters.

Features

- Low collector-to-emitter saturation voltage: VCE(sat)=-0.5V (PNP), 0.4V (NPN) max.
- · Wide ASO and highly registant to breakdown.
- · Micaless package facilitating easy mounting.

Specifications (): 2SB1508

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)50	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)12	Α
Collector Current (Pulse)	ICP		(-)25	Α
Collector Dissipation	PC		3.0	W
		Tc=25°C	45	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =(-)40V, I _E =0A			(-)0.1	mA
Emitter Cutoff Current	IEBO	VEB=(-)4V, IC=0A			(-)0.1	mA
DC Current Gain	hFE1	V _{CE} =(-)2V, I _C =(-)1A	70*		280*	
	hFE2	V _{CE} =(-)2V, I _C =(-)5A	30			
Gain-Bandwidth Product	fŢ	V _{CE} =(-)5V, I _C =(-)1A		10		MHz

Continued on next page.

^{*:} The 2SBB1508 / 2SD2281 are classified by 1A hFE as follows:

Rank	Q	R	S		
hFE	70 to 140	100 to 200	140 to 280		

- Any and all SANYO Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO Semiconductor representative nearest you before using any SANYO Semiconductor products described or contained herein in such applications.
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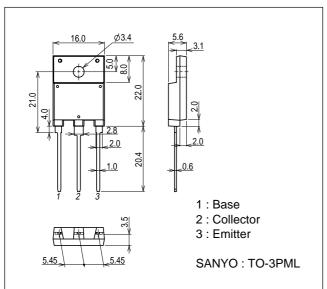
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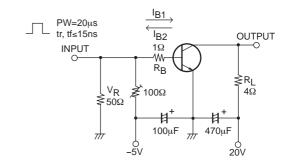
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=(-)6A, IB=(-)0.3A			(-0.5)0.4	٧
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)1mA, I _E =0A	(-)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=(-)1mA, RBE=∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=(-)1mA, IC=0A	(-)6			V
Turn-ON Time	ton	See specified Test Circuit.		(0.2)0.1		μS
Storage Time	tstg	See specified Test Circuit.		(0.4)1.2		μS
Fall Time	tf	See specified Test Circuit.		(0.1)0.5		μS

Package Dimensions

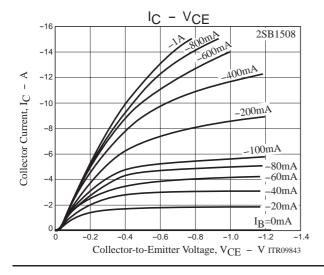
unit : mm (typ) 7505-002

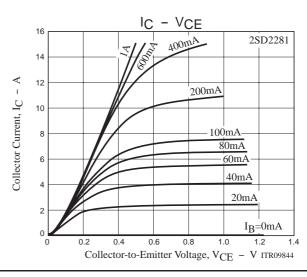


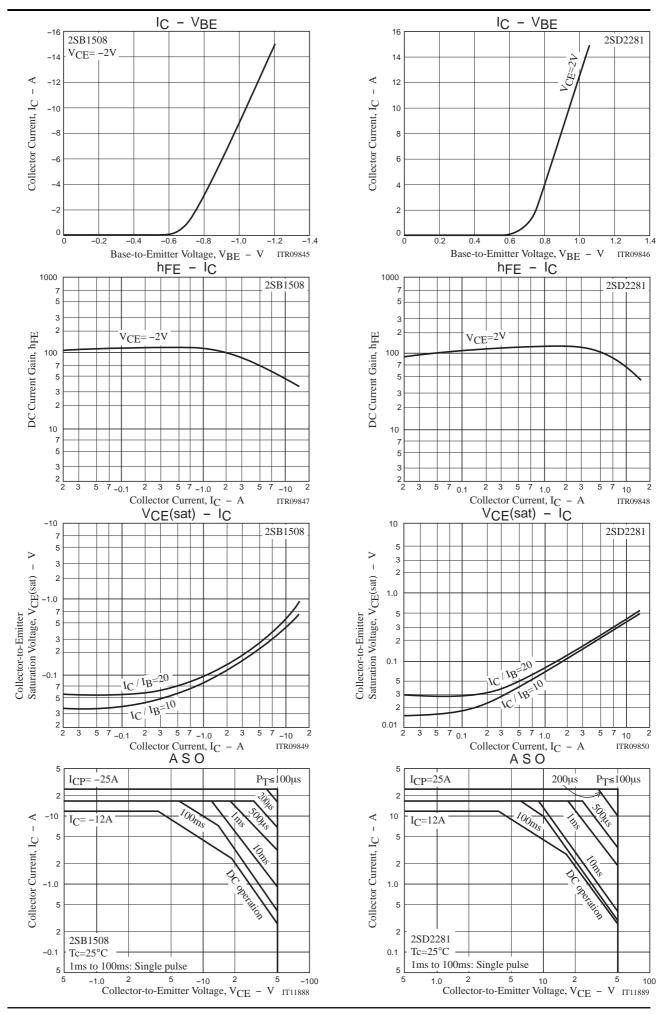
Switching Time Test Circuit



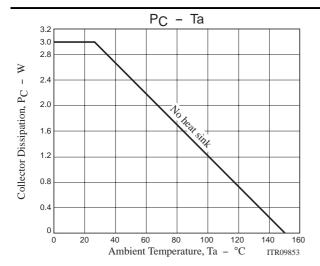
 $10I_{B1}$ = $-10I_{B2}$ = I_{C} =5AFor PNP, the polarity is reversed.

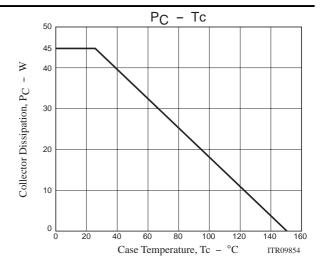






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